

CHAPTER 0

Revision of Electronics 1

A : Leis de Kirchhoff

$$\sum I = 0$$

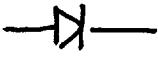


cargas não desaparecem

$$\sum V = 0$$

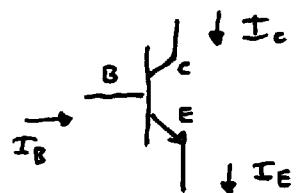


voltar ao inicio:
mesura tensão

B : 
diodo aberto : $\Delta V \approx 0.7$, $I > 100 \mu A$
 fechado : $I \approx 10^{-14} A (\approx 0)$

(junction)

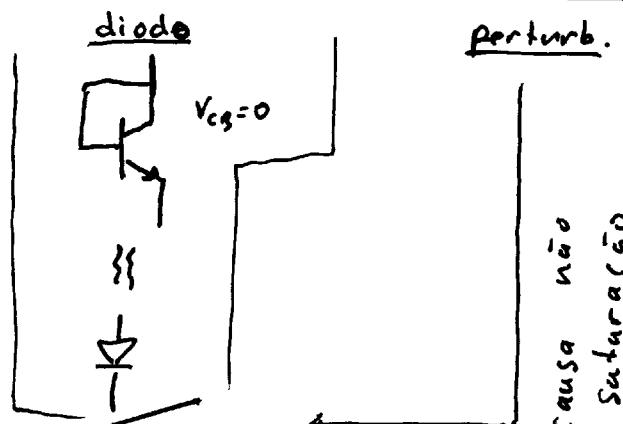
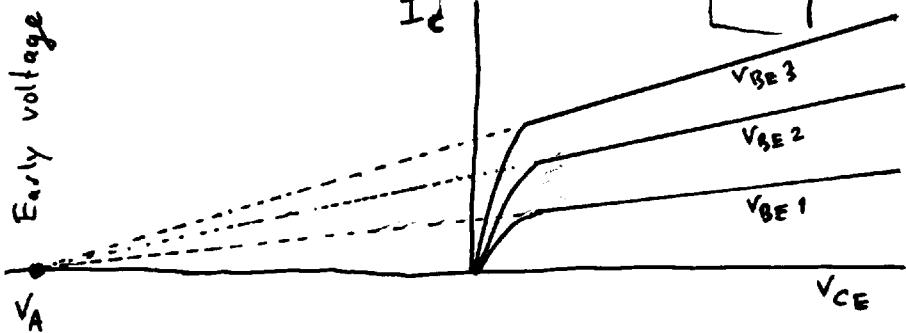
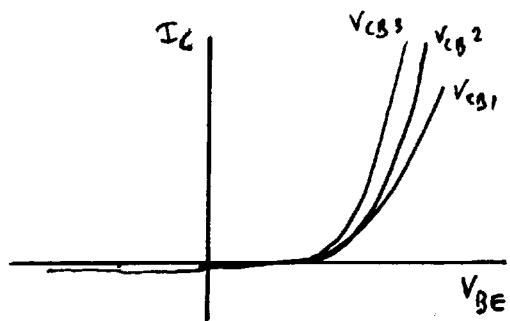
C : transistor is current amplifier



$$\begin{aligned} I_E &= (\beta + 1) I_B \\ I_C &= \beta I_B \\ I_E &= \alpha I_E \end{aligned} \quad \left. \begin{array}{l} \text{(Kirchhoff)} \\ \text{I}_C + \text{I}_B = \text{I}_E \end{array} \right\} \quad \alpha = \frac{\beta}{\beta + 1} \approx 1$$

typical : $\beta = 100$, $\alpha = 0.99$

D : Ebers - Moll : $I_C = I_0 \left[\exp\left(\frac{q}{kT} V_{BE}\right) - 1 \right] + I_s \left[\exp\left(\frac{q}{kT} V_{CB}\right) - 1 \right]$



causa não
saturação
 V_A , etc.

E : simplificação

$$I_E = I_0 \left[\exp\left(\frac{q}{kT} V_{BE}\right) - 1 \right]$$

$I_0 \approx 10^{-14} A$ reverse-bias-leakage current
($V_{BE} = -\infty$, $I_E = -I_0$)

$$I_E \approx I_0 \exp\left(\frac{q}{kT} V_{BE}\right) = I_0 \exp\left(\frac{V_{BE}}{V_T}\right) \quad V_T \equiv \frac{kT}{q}$$

corrente típica : 7 mA , $T = 300 \text{ K}$ ($V_T = 26 \text{ mV}$)

$V_{BE} = V_T \ln\left(\frac{I_E}{I_0}\right)$:	0.60 V	\leftrightarrow	100 μA
		0.66 V	\leftrightarrow	1 mA
		0.72 V	\leftrightarrow	10 mA
		0.78 V	\leftrightarrow	100 mA

Transistor aberto $\leftrightarrow V_{BE} = 0.7 \text{ V}$

F : Resistência de entrada

$$r_i \equiv \frac{1}{\partial I_i / \partial V_i}$$

dinâmico

$$\text{example : } V_i = V_{BE}$$

$$I_i = I_B = \frac{1}{(\beta+1)} I_E$$

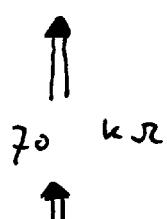
$$\frac{\partial I_i}{\partial V_i} = \frac{1}{(\beta+1)} \frac{\partial I_E}{\partial V_{BE}} = \frac{I_0}{(\beta+1)V_T} \exp\left(\frac{V_{BE}}{V_T}\right) = \frac{I_E}{(\beta+1)V_T}$$

$$r_i = (\beta+1) \frac{V_T}{I_E} = (\beta+1) r_e = r_{\pi} \quad 2.6 \text{ k}\Omega$$

$$R_i \equiv \frac{1}{\partial I_i / \partial V_i}$$

estático

$$\text{example : } R_i = \frac{1}{\partial I_i / \partial V_i} = \frac{1}{(\beta+1)V_{BE}}$$



$$\text{note : } g_m \equiv \frac{\partial I_{out}}{\partial V_i} = \frac{\beta \partial I_i}{\partial V_i} = \frac{\beta}{\beta+1} \cdot \frac{1}{r_e}$$

example com
 $\beta = 100$, $V_{BE} = 0.7$,
 $1 \text{ mA} = I_E$

r_e is a parameter that describes the dynamic response to a signal input (δV_i). It is not a real resistance!

$$r_e \equiv \frac{V_T}{I_E} \quad (\text{depends on bias } I_E \text{ and temperature})$$

$$v_i = \delta V_i$$

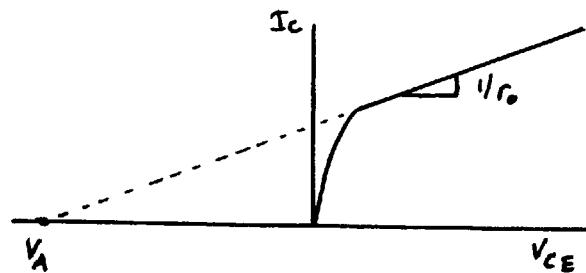
G : Resistência de Saída

$$r_o \equiv \frac{1}{\frac{\partial I_o}{\partial V_o}}$$

exemplo : transistor

$$I_o = I_c$$

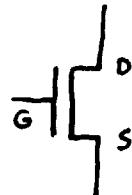
$$V_o = V_c = V_{CE}$$



$$\frac{\partial I_o}{\partial V_o} = \frac{\partial I_c}{\partial V_{CE}} = \frac{I_c}{V_{CE} + V_A}$$

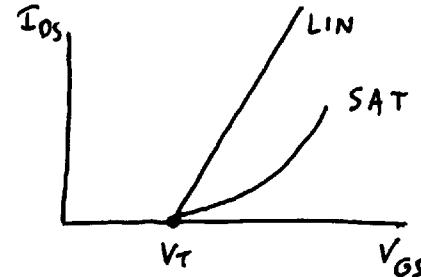
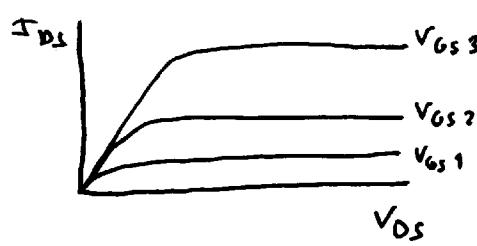
$$r_o \sim \frac{V_A}{I_c}, \text{ ex } \frac{200 \text{ V}}{1 \text{ mA}} = 200 \text{ k}\Omega$$

H : Field - Effect Transistor



$$LIN : I_{DS} = C_{ox} \gamma \frac{W}{L} (V_{GS} - V_T) V_{DS}$$

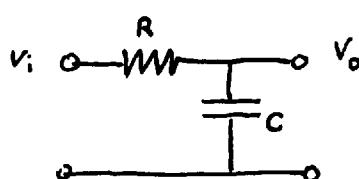
$$SAT : I_{DS} = \frac{1}{2} C_{ox} \gamma \frac{W}{L} (V_{GS} - V_T)^2$$



$$r_o = \frac{1}{\frac{\partial I_{DS}}{\partial V_{DS}}} = \infty$$

$$r_i = \frac{1}{\frac{\partial I_G}{\partial V_{DS}}} = \infty \quad (I_{GS}=0)$$

I : Filtros



"em altas frequências um C é um curto-circuito"
"em baixas frequências um C é um circuito-aberto"

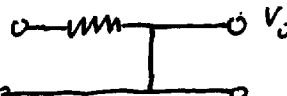
(low-pass filter)



baixas - freq.

$$V_o = V_i$$

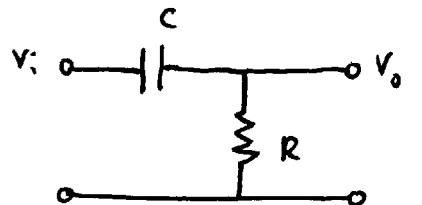
$$f_c$$



altas - freq.

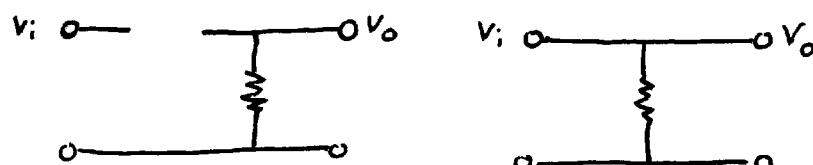
$$V_o = 0$$

$$\text{ponto de comutação: } f_c = \frac{1}{2\pi RC}$$



(HPF)

(high-pass filter)



baixas - freq.

$$V_o = 0$$

$$\leftrightarrow$$

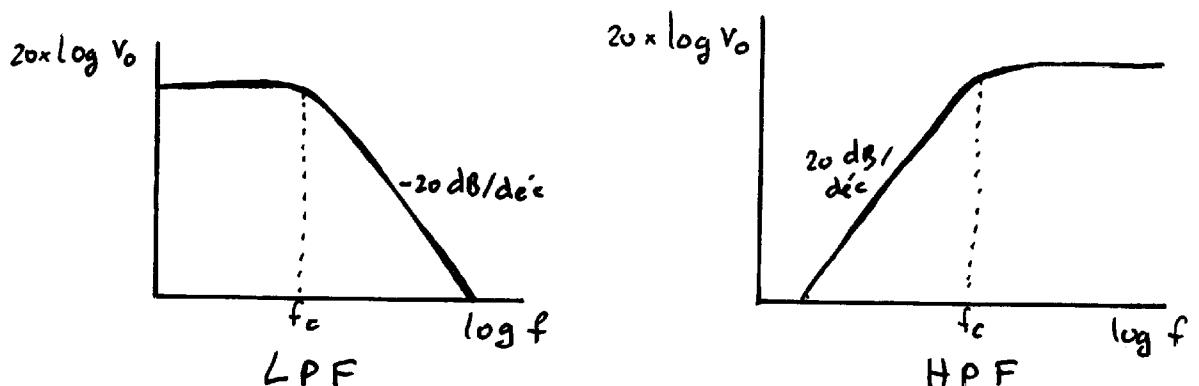
altas - freq

$$f_c$$

$$V_o = V_i$$

$$\text{Ponto de comutação} \quad f_c = \frac{1}{2\pi RC}$$

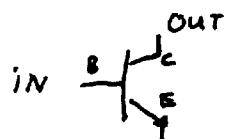
J: Bode plots ($20 \times \log V_o - \log f$)



$$\text{em } f_c : \quad V_o = \frac{1}{\sqrt{2}} V_o^{\max} \quad (P_o = \frac{1}{2} P_o^{\max})$$

$$\log V_o = -3 \text{ dB} \quad (20 \log \frac{1}{\sqrt{2}} = -3 \text{ dB})$$

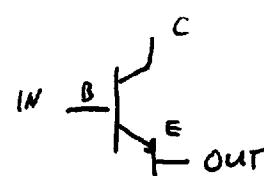
M: SIMPLE CIRCUITS



COMMON
EMITTER

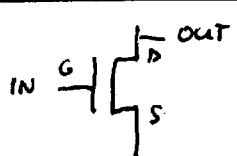


COMMON
BASE

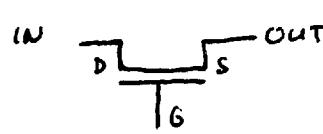


COMMON
COLLECTOR

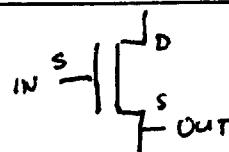
Small-signal amplifiers are named after the terminal that has neither input nor output



COMMON
SOURCE



COMMON
GATE



COMMON
DRAIN

K: Transfer functions

$$T(f) \equiv V_o(f) / V_i(f) \quad \text{or} \quad T(s) = V_o / V_i$$

$s = j\omega$

	LPF	
$T(s)$	$\frac{1}{1 + s/\omega_0}$	$H.P.F$

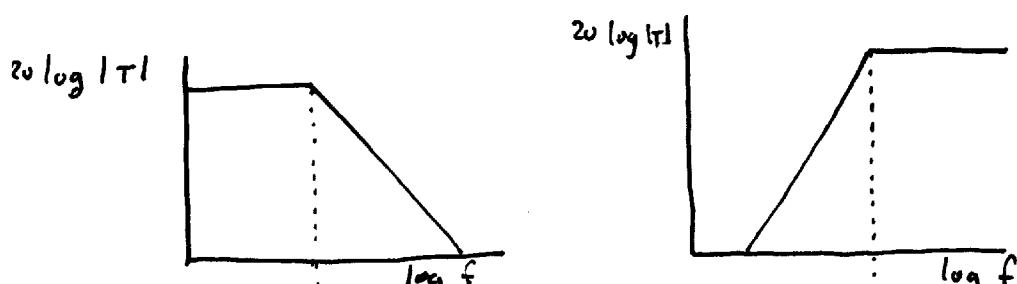
$T(\omega)$	$\frac{1}{1 + j\omega/\omega_0}$	$\frac{1}{1 - j\omega_0/\omega}$

$ T(\omega) $	$\frac{1}{\sqrt{1 + (\omega/\omega_0)^2}}$	$\frac{1}{\sqrt{1 + (\omega_0/\omega)^2}}$

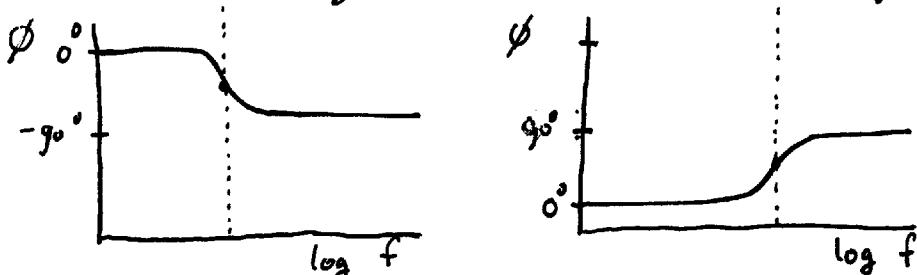
$\omega = 0$	1	0
$\omega = \infty$	0	1
$\omega = \omega_0$	$ T = \frac{1}{\sqrt{2}}, \phi = -45^\circ$	$ T = \frac{1}{\sqrt{\omega}}, \phi = +45^\circ$
$\omega \ll \omega_0$	1	(20 dB/dec)

$\omega \gg \omega_0$	$\sim 1/\omega$ (-20 dB/dec)	1
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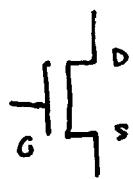
$\omega_0 =$	$\frac{1}{RC}$	$\frac{1}{RC}$
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Bode
Plots

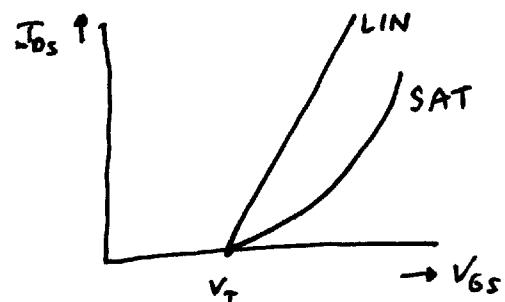
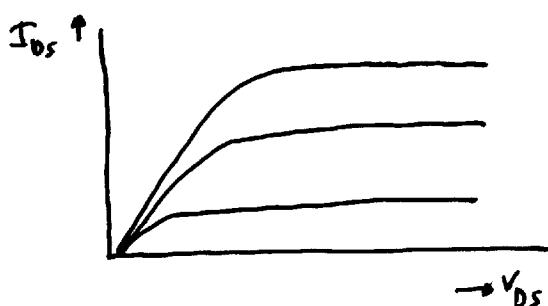


H: Field - Effect Transistor



$$\text{LIN : } I_{ds} = C_ox \gamma \frac{W}{L} (V_{GS} - V_T) V_{DS} = \lambda (V_{GS} - V_T) V_{DS}$$

$$\text{SAT : } I_{ds} = \frac{1}{2} C_ox \gamma \frac{W}{L} (V_{GS} - V_T)^2 = \frac{1}{2} \lambda (V_{GS} - V_T)^2$$



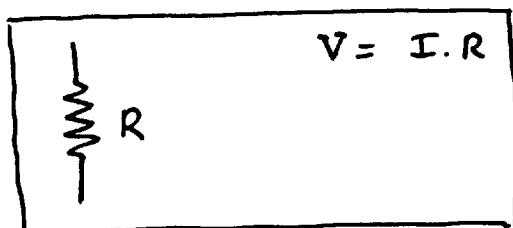
$$r_o = \left| \frac{\partial I_{DS}}{\partial V_{DS}} \right|_{V_{GS}=\text{const.}} = \infty, \quad r_i = \left| \frac{\partial I_G}{\partial V_{GS}} \right|_{V_{DS}=\text{const.}} = \infty \quad (I_{GS}=0)$$

(no leakage current or polarization current !)

$$g_m = \left. \frac{\partial I_{DS}}{\partial V_{GS}} \right|_{V_{DS}=\text{const.}} = \lambda V_{DS} \quad (\text{LIN})$$

$$= \lambda V_{GS} \quad (\text{SAT})$$

L: components analyzed



$V = I \cdot R$ → A resistance is a linear element that translates current to voltage

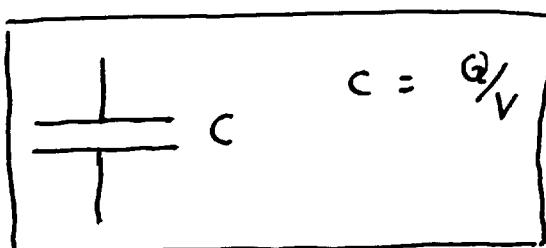
$$I \rightarrow V$$

→ A resistance defines a current

$$V \rightarrow I$$

$$\partial V = R \cdot \partial I$$

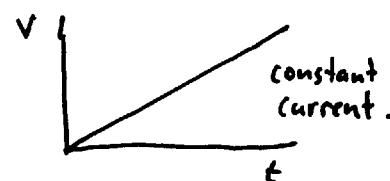
$$(V = R \cdot i)$$



$C = Q/V$ → A capacitor is a charge storage "how much charge stored per volt" → is "integrator" $V \rightarrow Q$

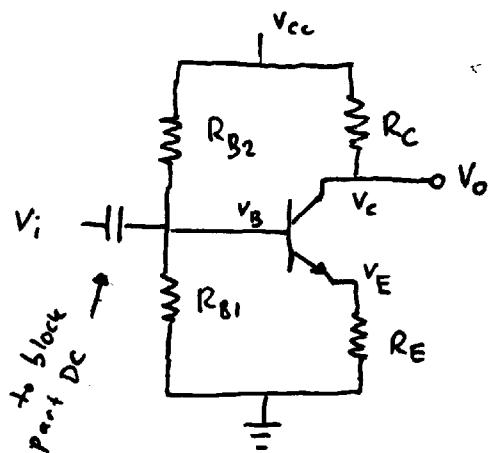
$$Q \rightarrow V$$

$$\int Idt \rightarrow V$$



Example Common-emitter amplifier

PART 1B



$$\beta = 100$$

$$R_{B1} = R_{B2} = 10 \text{ k}\Omega$$

$$R_E = 3.3 \text{ k}\Omega$$

$$R_C = 3.3 \text{ k}\Omega$$

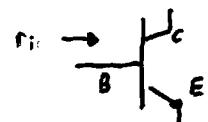
$$V_{cc} = +10 \text{ V}$$

POLARIZATION / BIAS

1) V_B ?

Assumption r_{in} at transistor $\gg 10 \text{ k}$
why?

$$r_{in} = r_\pi + R_E ? \quad \text{No!}$$



$$r_{in} = r_\pi + (\beta+1) R_E !$$

remember: $r_{in} \equiv 1 / \frac{\partial I_B}{\partial V_B}$

$$\frac{\partial I_B}{\partial V_B} = \frac{\frac{1}{\beta+1} \frac{\partial I_E}{\partial (V_E + 0.7 \text{ V})}}{\frac{\partial (V_E + 0.7 \text{ V})}{\partial V_E}} = \frac{1}{\beta+1} \frac{\partial I_E}{\partial V_E} = \frac{1}{(\beta+1) R_E}$$

(implies $r_\pi = 0$)

$$r_{in} = (\beta+1) R_E$$

total (including r_π): $r_{in} = r_\pi + (\beta+1) R_E$

Order $1 \text{ k}\Omega$ Order $100 \text{ k}\Omega$

O transistor funciona como uma lente. Vista da base, as resistências (e outros componentes) aparecem ampliadas.



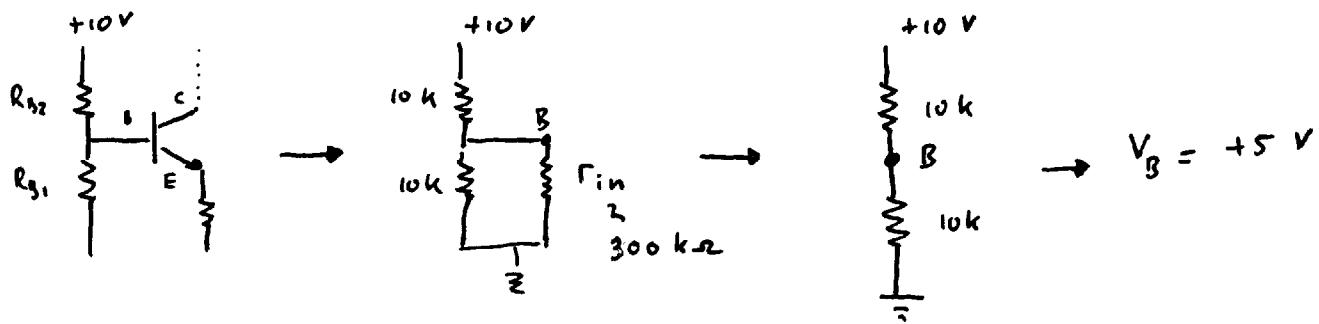
$$(\beta+1) R_E \leftarrow R_E$$

Vista do emissor, os componentes na base aparecem reduzidos



$$R_B \rightarrow \frac{R_B}{\beta+1}$$

$r_{in} \gg R_B$



$$V_B = \frac{R_{B1}}{R_{B1} + R_{B2}} \cdot V_{CC} = \frac{10 \text{ k}\Omega}{10 \text{ k}\Omega + 10 \text{ k}\Omega} \cdot 10 \text{ V} = 5 \text{ V}$$

$$V_E = V_B - 0.7 \text{ V} \quad (\text{in case transistor open. check at end!})$$

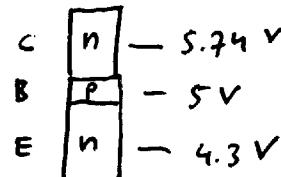
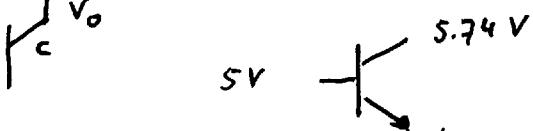
$$= 4.3 \text{ V}$$

$$I_E = V_E / R_E = 1.30 \text{ mA}$$

$$I_B = I_E / (\beta + 1) = 12.9 \mu\text{A}$$

$$I_C = \alpha I_E = 1.29 \text{ mA}$$

$$V_{CC} = +10 \text{ V} \quad V_o = V_{CC} - R_C \cdot I_C = 10 - 3.3 \text{ k}\Omega \times 1.29 \text{ mA} = 5.74 \text{ V}$$



A properly working transistor has the C-B biased reverse and the B-E junction in forward. Forward bias : N = negative, P = positive. Thus, the above transistor is working correct.

$$r_e = \frac{V_T}{I_E} = \frac{26 \text{ mV}}{1.30 \text{ mA}} = 20 \text{ }\Omega$$

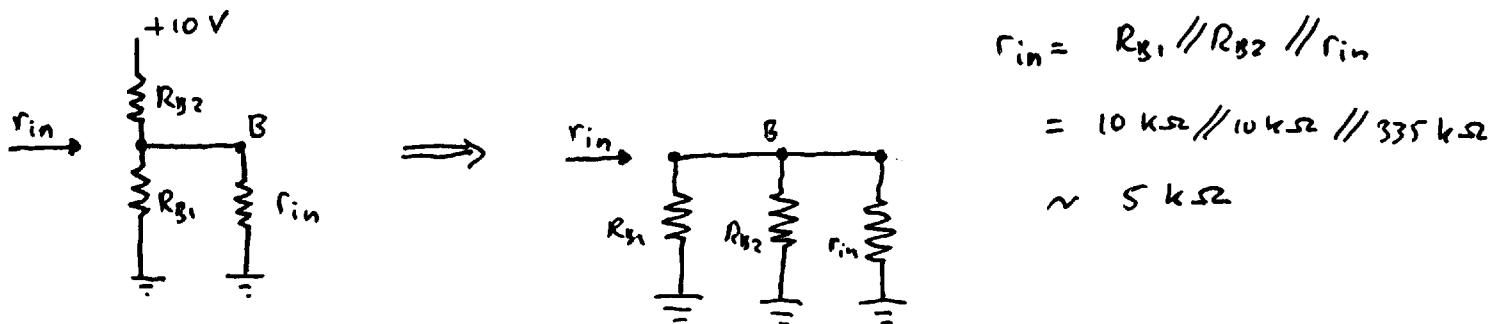
$$r_\pi = (\beta + 1) r_e = (100 + 1) 20 \text{ }\Omega = 2 \text{ k}\Omega$$

$$r_{in} = r_\pi + (\beta + 1) R_E = 335 \text{ k}\Omega$$

Total dynamic input resistance of amplifier:

For AC signals : any DC power supply point
is equal to $\frac{1}{\text{load}}$ (and current source = open)

(because $v (= \delta v) \equiv 0$!)



AC signal amplification :

$$r_i = r_\pi + (\beta+1)R_E$$

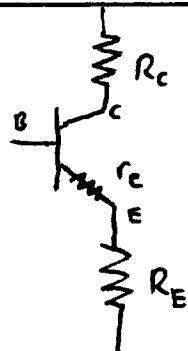
$$r_i \equiv \frac{1}{\frac{\partial I_B}{\partial V_B}} \Rightarrow \frac{\partial I_B}{\partial V_B} = \frac{\partial V_B}{r_i} = \frac{\partial V_B}{r_\pi + (\beta+1)R_E}$$

$$I_c = \beta I_B \Rightarrow \frac{\partial I_c}{\partial V_B} = \beta \frac{\partial I_B}{\partial V_B} = \frac{\beta \partial V_B}{r_\pi + (\beta+1)R_E}$$

$$v_o = V_C - R_C I_C \Rightarrow$$

$$\frac{\partial V_o}{\partial V_B} = -R_C \frac{\partial I_C}{\partial V_B} = -\frac{\beta R_C}{r_\pi + (\beta+1)R_E} \cdot \frac{\partial V_B}{\partial V_B}$$

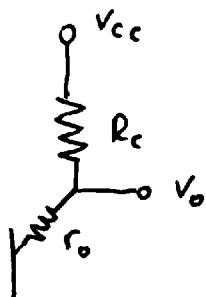
$$A = \frac{v_o}{v_B} = \frac{\partial V_o}{\partial V_B} = -\frac{R_C}{r_e + R_E} \quad (r_\pi = (\beta+1)r_e, \beta \approx (\beta+1))$$



The gain of a common-emitter amplifier is all resistance at collector
divided by all resistance at emitter
with minus sign

$$A = -\frac{3300}{20 + 3300} \approx -1$$

Output resistance of amplifier



r_o is resistance of transistor
(with E connected to ground !!)

$$r_o \approx 200 \text{ k}\Omega \text{ (p.3)}$$

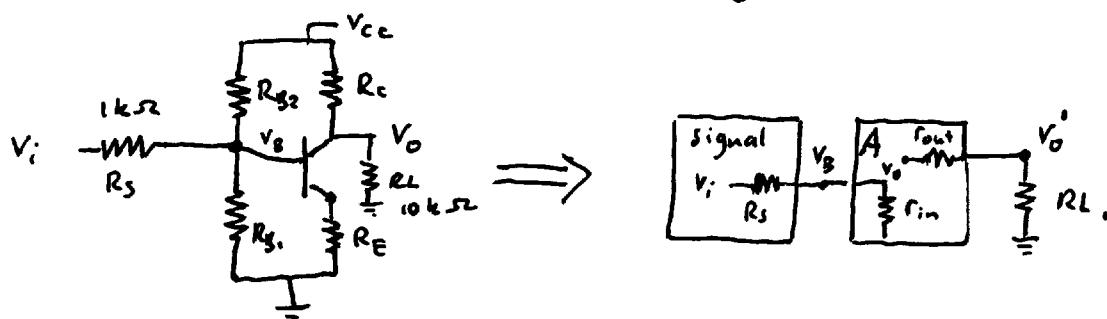
$$(r_o \gg R_c)$$

r_{out} of transistor in Com. Em. is MUCH
larger than r_o (something like $\beta \times r_o$)
(see p.7 of ch. 1)



Combining amplifier stages

imagine signal source has $1 \text{ k}\Omega$ output resistance and
a $10 \text{ k}\Omega$ load resistance is at output
what will be the total gain of circuit?



$$R_s = 1 \text{ k}\Omega, r_{in} = 5 \text{ k}\Omega \text{ (p.7)}, R_L = 10 \text{ k}\Omega$$

$$A = -1 \text{ (p.7)}, r_{out} = 3.3 \text{ k}\Omega \text{ (p.8)}$$

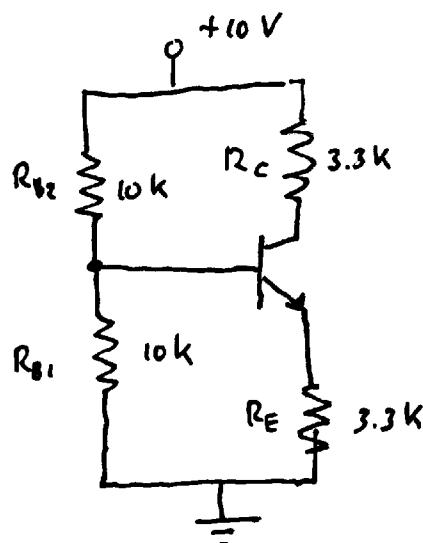
$$A_{tot} = \frac{V'_o}{V_i} = \frac{V'_o}{V_o} \cdot \frac{V_o}{V_B} \cdot \frac{V_B}{V_i}$$

$$\begin{aligned} \frac{V'_o}{V_o} &= \frac{R_L}{R_L + r_{out}}, \quad \frac{V_o}{V_B} = A, \quad \frac{V_B}{V_i} = \frac{r_{in}}{r_{in} + R_s} \\ &= 0.429 \quad = -1 \quad = 0.833 \end{aligned}$$

$$A_{tot} = 0.429 \times -1 \times 0.833 = -0.357$$

DC power consumption of amplifier

$$P = I^2 R \text{ or } V^2/R \text{ or } VI$$



$$R_{B1} : V = 5V, R = 10k \Rightarrow P = 2.5 \text{ mW}$$

$$R_{B2} : V = 5V, R = 10k \Rightarrow P = 2.5 \text{ mW}$$

$$R_E : V = 4.3V, R = 3.3k \Rightarrow P = 5.6 \text{ mW}$$

$$R_C : V = 4.3V, R = 3.3k \Rightarrow P = 5.6 \text{ mW}$$

$$\text{* trans: } V = 0.7V, I = 1.29 \text{ mA} \Rightarrow P = 0.90 \text{ mW}$$

total

$$P = 17.1 \text{ mW}$$

Note: there is power loss at every part where we have a voltage drop and a current simultaneously. You can also say: where there is a current and a resistance. The heat generated in the transistor is not much in this case, but other amplifiers will lose a lot of power in the transistors and have to be cooled.

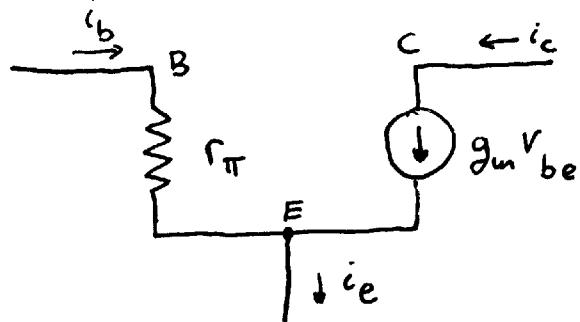
*: note that we cannot use r_e or r_π here because they are for signals (AC) only.

Alternative calculation: The +10V power supply supplies a total current of 1.29 mA through R_C plus 0.5 mA ($\frac{+10V}{10k+10k}$) through the base resistors. Total: 1.79 mA. $P = V \cdot I = 17.9 \text{ mW}$

N: Small - signal models of transistors and amplifiers.

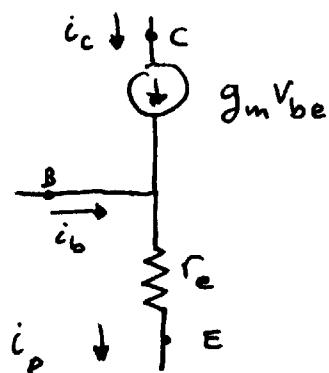
Although electronic circuits can be analyzed without the help of small-signal models, in some cases those small-signal model can help to understand things. Examples of ^{npn}BJT models

||
"base oriented"
HYBRID- π

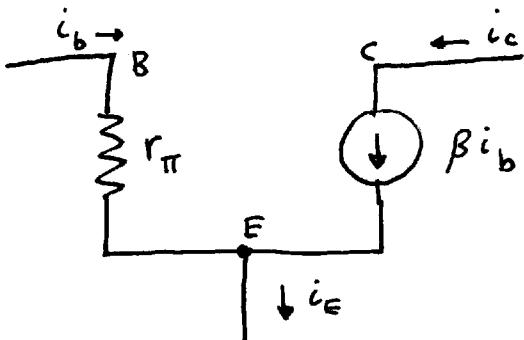


Hybrid- π model with
voltage-controlled
current source

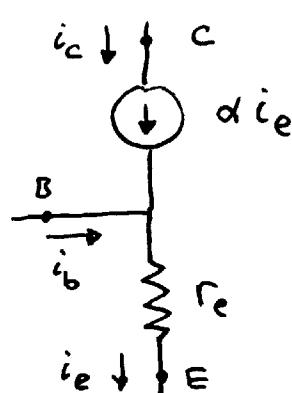
||
"emitter oriented"
T MODEL



T model with voltage -
controlled current source



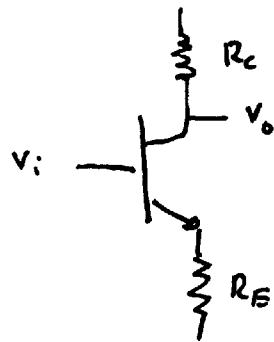
Hybrid- π model with
current controlled
current source



T model with current
controlled current source

O: BASIC BJT AMPLIFIERS

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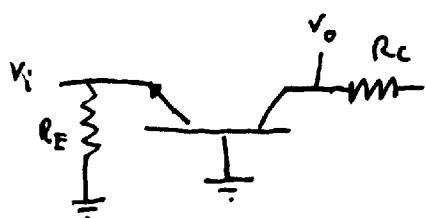


COMMON - Emitter AMPLIFIER (CEA)

$$\text{signal gain : } \frac{V_o}{V_i} = - \frac{R_C}{r_e + R_E}$$

$$r_{in} = (\beta + 1) (r_e + R_E)$$

$$r_{out} = R_C$$

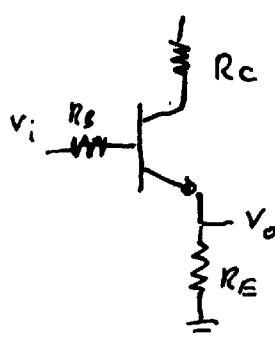


COMMON - BASE AMPLIFIER (CBA)

$$\text{gain } \frac{V_o}{V_i} = + \frac{R_C}{r_e}$$

$$r_{in} = r_e // R_E$$

$$r_{out} = R_C$$



COMMON - COLLECTOR AMPLIFIER (CCA)

$$\text{gain } \frac{V_o}{V_i} = R_E / (r_e + R_E) \approx 1$$

$$r_{in} = (\beta + 1) (r_e + R_E) + R_B$$

$$r_{out} = R_E // \left(\frac{R_B}{\beta + 1} + r_e \right)$$